

TO-92S Plastic-Encapsulate Transistors

KSD1020 TRANSISTOR (NPN)

FEATURES

- General Purpose Switching Application

APPLICATIONS

- Audio Frequency Amplifier

TO – 92S

- EMITTER
- COLLECTOR
- BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	0.7	A
P _C	Collector Power Dissipation	350	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	357	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA, I _C =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =30V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =20V, I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)} *	V _{CE} =1V, I _C =100mA	120		400	
	h _{FE(2)}	V _{CE} =1V, I _C =700mA	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =700mA, I _B =70mA			0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =700mA, I _B =70mA			1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =6V, I _C =10mA	0.6		0.7	V
Collector output capacitance	C _{ob}	V _{CB} =6V, I _E =0, f=1MHz			25	pF
Transition frequency	f _T	V _{CE} =6V, I _C =10mA	50			MHz

*Pulse test

CLASSIFICATION OF h_{FE(1)}

RANK	Y	G
RANGE	120-240	200-400